SHEET 1	OF	_1_
PLICATION NO.		

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTORNEY'S DKT	APPLICATION NO.
015290-517	09/788,365
APPLICANT	
Tuqiang NI t al.	Ĭ
FILING DATE	GROUP
February 21, 2001	1763

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

	SHEET OF _1
ATTORNEY'S DKI INO.	APPLICATION NO.
015290-517	09/788,365
APPLICANT	
Tuqiang NI et al.	
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